

H2 Sub I. 125. (Amended) The imaging device according to claim 115, wherein said first insulating layer is a layer of silicon dioxide.

Please replace claim 130 with the following rewritten claim 130:

H3 Sub I. 130. (Amended) The imaging device according to claim 120, wherein each of said photogate and said nitrogen containing second insulating layer is only partially disposed over each of said first and second gate stacks.

Please replace claim 135 with the following rewritten claim 135:

H4 Sub I. 135. (Twice amended) The imaging device according to claim 120, wherein said first gate stack is a transfer gate stack and said second gate stack is a reset gate stack.

Please replace claim 140 with the following rewritten claim 140:

H5 Sub I. 140. (Twice amended) The imaging device according to claim 135, wherein said nitrogen containing second insulating layer is disposed over a portion of said transfer gate stack.

REMARKS

Reconsideration and allowance of this application, as amended, are respectfully requested. Claims 120, 125, 130, 135, and 140 have been amended. Claims 1-4, 7-15, 18-23, 25-29, 31-39, 41-63, 65, 66, and 115-144 remain pending in the application. The